

SN74AVC2T45 2-Bit, Dual Supply, Bus Transceiver with Configurable Level-Shifting and Translation

1 Features

- Available in the Texas Instruments NanoFree[™] Package
- V_{CC} Isolation Feature: If Either V_{CC} Input Is at GND, Both Ports Are in the High-Impedance State
- Dual Supply Rail Design
- I/Os Are 4.6V Over Voltage Tolerant
- Ioff Supports Partial-Power-Down Mode Operation
- Max Data Rates
 - 500Mbps (1.8V to 3.3V)
 - 320Mbps (<1.8V to 3.3V)
 - 320Mbps (Level-Shifting to 2.5V or 1.8V)
 - 280Mbps (Level-Shifting to 1.5V)
 - 240Mbps (Level-Shifting to 1.2V)
- Latch-Up Performance Exceeds 100mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22

2 Applications

- Smartphones
- Servers
- Desktop PCs and notebooks
- Other portable devices

3 Description

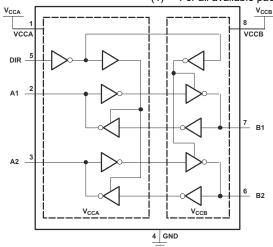
This 2-bit non-inverting bus transceiver uses two separate configurable power-supply rails. The A ports are designed to track V_{CCA} and accepts any supply voltage from 1.2V to 3.6V. The B ports are designed to track V_{CCB} and accepts any supply voltage from 1.2V to 3.6V. This allows for universal low-voltage bidirectional translation and level-shifting between any of the 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V voltage nodes.

The SN74AVC2T45 is designed for asynchronous communication between two data buses. The logic levels of the direction-control (DIR pin) input activate either the B-port outputs or the A-port outputs. The device transmits data from the A bus to the B bus when the B-port outputs are activated and from the B bus to the A bus when the A-port outputs are activated. The input circuitry on both A and B ports always is active and must have a logic HIGH or LOW level applied to prevent excess leakage current on the internal CMOS structure.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)			
SN74AVC2T45DCT	DCT, (SSOP, 8)	2.95mm × 2.80mm			
SN74AVC2T45DCU	DCU (VSSOP, 8)	2.30mm × 2.00mm			
SN74AVC2T45YZP	YZP (DSBGA, 8)	1.89mm × 0.89mm			
SN74AVC2T45DDF	DDF (SOT-23, 8)	2.90mm × 1.60mm			

(1) For all available packages, see Section 11.



A. Pin numbers are for the DCT and DCU packages only.

Logic Diagram (Positive Logic)



Table of Contents

1 Features	1
2 Applications	1
3 Description	1
4 Pin Configuration and Functions	
Pin Functions	3
5 Specifications	4
5.1 Absolute Maximum Ratings	4
5.2 ESD Ratings	
5.3 Recommended Operating Conditions	
5.4 Thermal Information	<mark>6</mark>
5.5 Electrical Characteristics	
5.6 Switching Characteristics: V _{CCA} = 1.2V	7
5.7 Switching Characteristics: V _{CCA} = 1.5V ±0.1V	7
5.8 Switching Characteristics: V _{CCA} = 1.8V ±0.15V.	<mark>8</mark>
5.9 Switching Characteristics: V _{CCA} = 2.5V ±0.2V	<mark>8</mark>
5.10 Switching Characteristics: V _{CCA} = 3.3V ±0.3V.	9
5.11 Operating Characteristics	9
5.12 Typical Characteristics	10
6 Parameter Measurement Information	
7 Detailed Description	13

7.1 Overview	13
7.2 Functional Block Diagram	13
7.3 Feature Description	
7.4 Device Functional Modes	
8 Application and Implementation	
8.1 Application Information	15
8.2 Typical Applications	
8.3 Power Supply Recommendations	17
8.4 Layout	
9 Device and Documentation Support	
9.1 Documentation Support	
9.2 Receiving Notification of Documentation Updates.	
9.3 Support Resources	
9.4 Trademarks	
9.5 Electrostatic Discharge Caution	19
9.6 Glossary	
10 Revision History	
11 Mechanical, Packaging, and Orderable	
Information	20



4 Pin Configuration and Functions

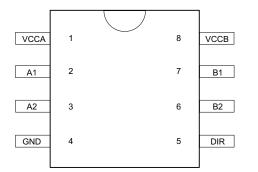


Figure 4-1. DCT or DCU Package 8-Pin SM8 or VSSOP Top View

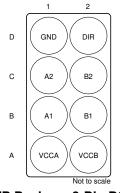


Figure 4-2. YZP Package 8-Pin DSBGA Bottom View

Pin Functions

	PIN			
NAME	NO. (SM8, VSSOP)	NO. (DSBGA)	TYPE ⁽¹⁾	DESCRIPTION
VCCA	1	A1	—	Supply Voltage A
VCCB	8	A2	_	Supply Voltage B
GND	4	D1	—	Ground
A1	2	B1	I/O	Output or input depending on state of DIR. Output level depends on V_{CCA} .
A2	3	C1	I/O	Output or input depending on state of DIR. Output level depends on V_{CCA} .
B1	7	B2	I/O	Output or input depending on state of DIR. Output level depends on V_{CCB} .
B2	6	C2	I/O	Output or input depending on state of DIR. Output level depends on V_{CCB} .
DIR	5	D2	I	Direction Pin, Connect to GND or to VCCA

(1) I = Input; O = Output; I/O = Input or Output



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT	
V _{CCA} V _{CCB}	Supply voltage		-0.5	4.6	V	
		IO ports (A port)	-0.5	4.6		
VI	Input voltage ⁽²⁾	IO ports (B port)	-0.5	4.6	V	
		Control inputs	-0.5	4.6		
v	Voltage applied to any output in the high-impedance or power-	A port	-0.5	4.6	V	
Vo	off state ⁽²⁾	B port	-0.5	4.6	v	
V	λ (alternative limit data and a structure limit data bindu an law state (2) (3)	A port	-0.5	V _{CCA} + 0.5	V	
Vo	Voltage applied to any output in the high or low state ^{(2) (3)}	B port	-0.5	V _{CCB} + 0.5	V	
I _{IK}	Input clamp current	V ₁ < 0		-50	mA	
I _{OK}	Output clamp current	V _O < 0		-50	mA	
I _O	Continuous output current			±50	mA	
	Continuous current through VCCA, VCCB, or GND			±100	mA	
TJ	Junction temperature			150	°C	
T _{stg}	Storage temperature		-65	150	°C	

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) The input negative-voltage and output voltage ratings can be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating can be exceeded up to 4.6 V maximum if the output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±8000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V
		Machine Model (MM), Per JEDEC specification JESD22-A115-A	±200	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.



5.3 Recommended Operating Conditions

See⁽³⁾ (4) (5)

			V _{CCI} ⁽¹⁾	V _{cco} ⁽²⁾	MIN	MAX	UNIT
V _{CCA}	Supply voltage				1.2	3.6	V
V _{CCB}	Supply voltage				1.2	3.6	V
			1.2V to 1.95V		V _{CCI} ⁽¹⁾ × 0.65		
VIH	High-level input voltage	Data inputs ⁽⁴⁾	1.95V to 2.7V		1.6		V
	input voltage	-	2.7 V to 3.6 V		2		
			1.2V to 1.95V		\ \	/ _{CCI} ⁽¹⁾ × 0.35	
VIL	Low-level input voltage	Data inputs ⁽⁴⁾	1.95V to 2.7V			0.7	V
	mput voltago		2.7V to 3.6V			0.8	
			1.2V to 1.95V		V _{CCA} × 0.65		
VIH	High-level input voltage	DIR (referenced to V _{CCA}) ⁽⁵⁾	1.95V to 2.7V		1.6		V
	input voltage		2.7V to 3.6V		2		
			1.2V to 1.95V			V _{CCA} × 0.35	
VIL	Low-level input voltage	DIR (referenced to V _{CCA}) ⁽⁵⁾	1.95V to 2.7V			0.7	V
	input voltago		2.7V to 3.6V			0.8	
VI	Input voltage				0	3.6	V
	Output valtage	Active state			0	V _{CCO} ⁽²⁾	V
Vo	Output voltage	3-state			0	3.6	v
	·			1.2V		-3	
		-		1.4V to 1.6V		-6	
I _{OH}	High-level output o	current		1.65V to 1.95V		-8	mA
		-		2.3V to 2.7V		-9	
				3V to 3.6V		–12	
	·			1.2V		3	
				1.4V to 1.6V		6	
I _{OL}	Low-level output c	urrent		1.65V to 1.95V		8	mA
	'			2.3V to 2.7V		9	
				3V to 3.6V		12	
Δt/Δv	Input transition rise	e or fall rate				5	ns/V
T _A	Operating free-air	temperature			-40	85	°C

(1) V_{CCI} is the voltage associated with the input port supply VCCA or VCCB.

(2) V_{CCO} is the voltage associated with the output port supply VCCA or VCCB.

(3) All unused data inputs of the device must be held at V_{CCI} or GND to provide proper device operation. See *Implications of Slow or Floating CMOS Inputs*.

(4) For V_{CCI} values not specified in the data sheet, V_{IH} min = $V_{CCI} \times 0.7V$, V_{IL} max = $V_{CCI} \times 0.3V$.

(5) For V_{CCI} values not specified in the data sheet, V_{IH} min = $V_{CCA} \times 0.7V$, V_{IL} max = $V_{CCA} \times 0.3V$.



5.4 Thermal Information

		SN74AVC2T45							
	THERMAL METRIC ⁽¹⁾	DCT (SM8)	DCU (VSSOP)	DDF (SOT-23)	YZP (DSBGA)	UNIT			
		8 PINS	8 PINS	8 PINS	8 PINS				
R _{θJA}	Junction-to-ambient thermal resistance	183.1	246.9	203.2	105.8	°C/W			
R _{0JC(top)}	Junction-to-case (top) thermal resistance	101.5	95.2	121.5	1.6	°C/W			
R _{θJB}	Junction-to-board thermal resistance	111.0	158.4	99.8	10.8	°C/W			
Ψ _{JT}	Junction-to-top characterization parameter	27.6	34.1	21.4	3.1	°C/W			
Ψ _{JB}	Junction-to-board characterization parameter	109.2	157.5	99.5	10.8	°C/W			

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)⁽¹⁾ (2)

PARAMETER		TEST CONDITIONS		V	V		T _A = 25°C		–40°C to +85°	с	UNIT	
		TESTCON	DITIONS	V _{CCA}	V _{CCB}	MIN	TYP	MAX	MIN	MAX	UNIT	
		I _{OH} = –100μA		1.2V to 3.6V	1.2V to 3.6V				$V_{CCO} - 0.2V$			
		I _{OH} = -3mA		1.2V	1.2V		0.95					
(3)		I _{OH} = -6mA		1.4V	1.4V				1.05		V	
V _{OH} ⁽³⁾		I _{OH} = -8mA	$V_{I} = V_{IH}$	1.65V	1.65V				1.2		v	
		I _{OH} = –9mA		2.3V	2.3V				1.75			
		I _{OH} = -12mA		3V	3V				2.3			
		I _{OL} = 100μA		1.2V to 3.6V	1.2V to 3.6V					0.2		
		I _{OL} = 3mA		1.2V	1.2V		0.25					
(3)	$I_{OL} = 6mA$ $I_{OL} = 8mA$		1.4V	1.4V					0.35	V		
VOL (0)		I _{OL} = 8mA	$V_{I} = V_{IL}$	1.65V	1.65V					0.45	V	
	I _{OL} = 9mA		2.3V	2.3V					0.55			
		I _{OL} = 12mA		3V	3V					0.7		
I	DIR	V _I = V _{CCA} or GNI)	1.2V to 3.6V	1.2V to 3.6V		±0.025	±0.25		±1	μA	
	A port		c) /	0V	0 to 3.6 V		±0.1	±1		±5		
off	B port	V_1 or V_0 = 0 to 3.	οv	0 to 3.6V	0V		±0.1	±1		±5	μA	
(3)	B port	V _O = V _{CCO} or GN	ID,	0V	3.6V		±0.5	±2.5		±5		
loz ⁽³⁾	A port	V _I = V _{CCI} or GND		3.6V	0V		±0.5	±2.5		±5	μA	
				1.2V to 3.6V	1.2V to 3.6V					10		
сса ⁽³⁾		V _I = V _{CCI} or GND	, I _O = 0	0V	3.6V					-2	μA	
				3.6V	0V					10		
				1.2V to 3.6V	1.2V to 3.6V					10		
I _{ССВ} <mark>(3)</mark>		V _I = V _{CCI} or GND	, I _O = 0	0V	3.6V					10	μA	
				3.6V	0V					-2		
_{CCA} + I (see Ta	ссв <mark>ble 5-1)</mark>	V _I = V _{CCI} or GND	, I _O = 0	1.2V to 3.6V	1.2V to 3.6V					20	μA	
Cı	Control inputs	V _I = 3.3V or GNE)	3.3V	3.3V		2.5				pF	
C _{io}	A or B port	V _O = 3.3V or GN	D	3.3V	3.3V		6				pF	

V_{CCO} is the voltage associated with the output port supply VCCA or VCCB. (1)

(2)

 V_{CCI} is the voltage associated with the input port supply VCCA or VCCB. V_{OH} : Output High Voltage; V_{OL} : Output Low Voltage; I_{OZ} : Hi-Z Output Current; I_{CCA} : Supply A Current; I_{CCB} : Supply B Current (3)



5.6 Switching Characteristics: V_{CCA} = 1.2V

PARAMETER	FROM	то	V _{CCB} = 1.2V	V _{CCB} = 1.5V	V _{CCB} = 1.8V	V _{CCB} = 2.5V	V _{CCB} = 3.3V	UNIT	
PARAMETER	(INPUT)	(OUTPUT)	ТҮР	ТҮР	ТҮР	ТҮР	ТҮР		
t _{PLH} ⁽²⁾	Α	В	3.1	2.6	2.4	2.2	2.2	20	
t _{PHL} ⁽²⁾		D	3.1	2.6	2.4	2.2	2.2	ns	
t _{PLH} ⁽²⁾	В	А	3.4	3.1	3	2.9	2.9		
t _{PHL} ⁽²⁾	D	A	3.4	3.1	3	2.9	2.9	ns	
t _{PHZ} ⁽²⁾	DIR	А	5.2	5.2	5.1	5	4.8		
t _{PLZ} ⁽²⁾	DIR	A	5.2	5.2	5.1	5	4.8	ns	
t _{PHZ} ⁽²⁾	DIR	В	5	4	3.8	2.8	3.2		
t _{PLZ} ⁽²⁾	DIR	D	5	4	3.8	2.8	3.2	ns	
t _{PZH} ⁽²⁾ (1)	סוס	٨	8.4	7.1	6.8	5.7	6.1		
t _{PZL} ⁽²⁾ (1)	DIR	A	8.4	7.1	6.8	5.7	6.1	ns	
t _{PZH} ⁽²⁾ (1)	סוס	В	8.3	7.8	7.5	7.2	7		
t _{PZL} ⁽²⁾ (1)	DIR	B	8.3	7.8	7.5	7.2	7	ns	

over recommended operating free-air temperature range, V_{CCA} = 1.2V (see Figure 6-1)

(1) The enable time is a calculated value, derived using the formula shown in the Section 8.2.2.2.1 section.

t_{PLH}: Low-to-high Propagation Delay; t_{PHL}: High-to-Low Propagation Delay; t_{PHZ}: High-to-Hi-Z Propagation Delay; t_{PLZ}: Low-to-Hi-Z Propagation Delay; t_{PLZ}: Hi-Z-to-High Propagation Delay; t_{PZL}: Hi-Z-to-Low Propagation Delay

5.7 Switching Characteristics: V_{CCA} = 1.5V ±0.1V

over recommended operating free-air temperature range, $V_{CCA} = 1.5V \pm 0.1V$ (see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = 1.2V	CCB = 1.2V V _{CCB} = 1.5V ± 0.1V		V _{CCB} = 1.8V ± 0.15V		V _{CCB} = 2.5V ± 0.2V		V _{CCB} = 3.3V ± 0.3V		UNIT	
		(001201)	ТҮР	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
t _{PLH} ⁽²⁾	А	В	2.8	0.7	5.4	0.5	4.6	0.4	3.7	0.3	3.5	ns	
t _{PHL} ⁽²⁾		В	2.8	0.7	5.4	0.5	4.6	0.4	3.7	0.3	3.5	115	
t _{PLH} ⁽²⁾	в	А	2.7	0.8	5.4	0.7	5.2	0.6	4.9	0.5	4.7	ns	
t _{PHL} ⁽²⁾		D	~	2.7	0.8	5.4	0.7	5.2	0.6	4.9	0.5	4.7	115
t _{PHZ} ⁽²⁾	DIR	А	3.9	1.3	8.5	1.3	7.8	1.1	7.7	1.4	7.6	ns	
t _{PLZ} ⁽²⁾	DIK	A	3.9	1.3	8.5	1.3	7.8	1.1	7.7	1.4	7.6	115	
t _{PHZ} ⁽²⁾	DIR	В	4.7	1.1	7	1.4	6.9	1.2	6.9	1.7	7.1	no	
t _{PLZ} ⁽²⁾	DIX	В	4.7	1.1	7	1.4	6.9	1.2	6.9	1.7	7.1	ns	
t _{PZH} ^{(2) (1)}	DIR	۸	7.4		12.4		12.1		11.8		11.8	ns	
t _{PZL} ⁽²⁾ ⁽¹⁾		R A	7.4		12.4		12.1		11.8		11.8	115	
t _{PZH} ^{(2) (1)}	סוס	В	6.7		13.9		12.4		11.4		11.1	20	
t _{PZL} ⁽²⁾ ⁽¹⁾	DIR	D	6.7		13.9		12.4		11.4		11.1	ns	

(1) The enable time is a calculated value, derived using the formula shown in the Section 8.2.2.2.1 section.

(2) t_{PLH}: Low-to-high Propagation Delay; t_{PLZ}: High-to-Low Propagation Delay; t_{PHZ}: High-to-Hi-Z Propagation Delay; t_{PLZ}: Low-to-Hi-Z Propagation Delay; t_{PZH}: Hi-Z-to-High Propagation Delay; t_{PZL}: Hi-Z-to-Low Propagation Delay

5.8 Switching Characteristics: V_{CCA} = 1.8V ±0.15V

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = 1.2V	V _{CCB} = 1.5V ± 0.1V		V _{CCB} = 1.8V ± 0.15V		V _{CCB} = 2.5V ± 0.2V		V _{CCB} = 3.3V ± 0.3V		UNIT	
			ТҮР	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
t _{PLH} ⁽²⁾	А	В	2.7	0.5	5.2	0.4	4.3	0.2	3.4	0.2	3.1	ns	
t _{PHL} ⁽²⁾		D	2.7	0.5	5.2	0.4	4.3	0.2	3.4	0.2	3.1	115	
t _{PLH} ⁽²⁾	В	А	2.4	0.7	4.7	0.5	4.4	0.5	4	0.4	3.8	ns	
t _{PHL} ⁽²⁾			~	2.4	0.7	4.7	0.5	4.4	0.5	4	0.4	3.8	115
t _{PHZ} ⁽²⁾	DIR	А	3.7	1.3	8.1	0.7	6.9	1.4	5.3	1.1	5.2	ns	
t _{PLZ} ⁽²⁾	DIK		3.7	1.3	8.1	0.7	6.9	1.4	5.3	1.1	5.2	115	
t _{PHZ} ⁽²⁾	DIR	В	4.4	1.3	5.8	1.3	5.9	0.8	5.7	1.5	5.9	ns	
t _{PLZ} ⁽²⁾	DIK	D	4.4	1.3	5.8	1.3	5.9	0.8	5.7	1.5	5.9	115	
t _{PZH} ⁽²⁾ (1)	פוח	Δ	6.8		10.5		10.3		9.7		9.7	ns	
t _{PZL} ⁽²⁾ (1)		DIR A	6.8		10.5		10.3		9.7		9.7	115	
t _{PZH} ⁽²⁾ (1)		В	6.4		13.3		11.2		8.7		8.3	n 0	
t _{PZL} ⁽²⁾ (1)	DIR	D	6.4		13.3		11.2		8.7		8.3	ns	

over recommended operating free-air temperature range, $V_{CCA} = 1.8V \pm 0.15V$ (see Figure 6-1)

(1) The enable time is a calculated value, derived using the formula shown in the Section 8.2.2.2.1 section.

(2) t_{PLH}: Low-to-high Propagation Delay; t_{PHL}: High-to-Low Propagation Delay; t_{PHZ}: High-to-Hi-Z Propagation Delay; t_{PLZ}: Low-to-Hi-Z Propagation Delay; t_{PLZ}: Low-to-Hi-Z Propagation Delay; t_{PLZ}: Hi-Z-to-High Propagation Delay; t_{PLZ}: Hi-Z-to-Low Propagation Delay

5.9 Switching Characteristics: V_{CCA} = 2.5V ±0.2V

over recommended operating free-air temperature range, $V_{CCA} = 2.5V \pm 0.2V$ (see Figure 6-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = 1.2V	V _{CCB} = ± 0.7		V _{CCB} = 1.8V ± 0.15V		V _{CCB} = 2.5V ± 0.2V		V _{CCB} = 3.3V ± 0.3V		UNIT		
	(INPUT)	(001201)	ТҮР	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX			
t _{PLH} ⁽²⁾	А	В	2.6	0.4	4.9	0.2	4	0.2	3	0.2	2.6	ns		
t _{PHL} ⁽²⁾	A	В	2.6	0.4	4.9	0.2	4	0.2	3	0.2	2.6	115		
t _{PLH} ⁽²⁾	В	А	2.1	0.6	3.8	0.5	3.4	0.4	3	0.3	2.8	ns		
t _{PHL} ⁽²⁾	D	D	D	A	2.1	0.6	3.8	0.5	3.4	0.4	3	0.3	2.8	115
t _{PHZ} ⁽²⁾	DIR	А	2.4	0.7	7.9	0.8	6.4	0.8	5	0.5	4.3	ns		
t _{PLZ} ⁽²⁾	DIK	A	2.4	0.7	7.9	0.8	6.4	0.8	5	0.5	4.3	4.3		
t _{PHZ} ⁽²⁾	DIR	В	3.8	1	4.3	0.6	4.3	0.5	4.2	1.1	4.1	20		
t _{PLZ} ⁽²⁾	DIK	D	3.8	1	4.3	0.6	4.3	0.5	4.2	1.1	4.1	ns		
t _{PZH} ^{(2) (1)}	DIR	А	5.9		8.5		7.7		7.2		6.9	20		
t _{PZL} ⁽²⁾ (1)	DIR	A	5.9		8.5		7.7		7.2		6.9	ns		
t _{PZH} ⁽²⁾ (1)	DIR	В	5		12.8		10.4		8		6.9	20		
t _{PZL} ⁽²⁾ (1)	UIR	0	5		12.8		10.4		8		6.9	ns		

(1) The enable time is a calculated value, derived using the formula shown in the Section 8.2.2.2.1 section.

(2) t_{PLH}: Low-to-high Propagation Delay; t_{PLZ}: High-to-Low Propagation Delay; t_{PLZ}: High-to-Hi-Z Propagation Delay; t_{PLZ}: Low-to-Hi-Z Propagation Delay; t_{PZH}: Hi-Z-to-High Propagation Delay; t_{PZL}: Hi-Z-to-Low Propagation Delay



5.10 Switching Characteristics: V_{CCA} = 3.3V ±0.3V

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = 1.2V		V _{CCB} = 1.5V ± 0.1V		V _{CCB} = 1.8V ± 0.15V		2.5V 2V	V _{CCB} = 3.3V ± 0.3V		UNIT		
			ТҮР	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX			
t _{PLH} ⁽²⁾	А	В	2.5	0.3	4.7	0.2	3.8	0.2	2.8	0.2	2.4	ns		
t _{PHL} ⁽²⁾	A	D	2.5	0.3	4.7	0.2	3.8	0.2	2.8	0.2	2.4	115		
t _{PLH} ⁽²⁾	В	А	2.1	0.6	3.6	0.4	3.1	0.3	2.6	0.3	2.4	ns		
t _{PHL} ⁽²⁾	D	A	2.1	0.6	3.6	0.4	3.1	0.3	2.6	0.3	2.4	115		
t _{PHZ} ⁽²⁾	DIR	А	2.9	1.1	8	1	6.5	1.3	4.7	1.2	4	20		
t _{PLZ} ⁽²⁾	DIK	A	A	2.9	1.1	8	1	6.5	1.3	4.7	1.2	4	ns	
t _{PHZ} ⁽²⁾	DIR	В	3.4	0.5	6.6	0.3	5.6	0.3	4.6	1.1	4.2	ns		
t _{PLZ} ⁽²⁾	DIK	D	3.4	0.5	6.6	0.3	5.6	0.3	4.6	1.1	4.2	115		
t _{PZH} ^{(2) (1)}	DIR	А	5.5		10.2		8.7		7.2		6.6	ns		
t _{PZL} ⁽²⁾ (1)	DIR	~	5.5		10.2		8.7		7.2		6.6	115		
t _{PZH} ^{(2) (1)}	DIP	В	5.4		12.7		10.3		7.5		6.4	20		
t _{PZL} ⁽²⁾ (1)	DIR	DIR	DIR	D	5.4		12.7		10.3		7.5		6.4	ns

over recommended operating free-air temperature range, $V_{CCA} = 3.3V \pm 0.3V$ (see Figure 6-1)

(1) The enable time is a calculated value, derived using the formula shown in the section.

(2) t_{PLH}: Low-to-high Propagation Delay; t_{PHL}: High-to-Low Propagation Delay; t_{PHZ}: High-to-Hi-Z Propagation Delay; t_{PLZ}: Low-to-Hi-Z Propagation Delay; t_{PLZ}: Low-to-Hi-Z Propagation Delay; t_{PLZ}: Hi-Z-to-High Propagation Delay; t_{PLZ}: Hi-Z-to-Low Propagation Delay

5.11 Operating Characteristics

T_A = 25°C

Р	ARAMETER	TEST	$\begin{array}{c} TEST \\ CONDITIONS \end{array} \begin{array}{c} V_{CCA} = \\ V_{CCB} = 1.2V \end{array} \begin{array}{c} V_{CCA} = \\ V_{CCB} = 1.5V \end{array}$		V _{CCA} = V _{CCB} = 1.8V	V _{CCA} = V _{CCB} = 2.5V	V _{CCA} = V _{CCB} = 3.3V	UNIT	
		CONDITIONS	TYP	TYP	ТҮР	TYP	ТҮР		
C (1)	A-port input, B-port output	C _L = 0, f = 10MHz,			3	3	4	pF	
C _{pdA} ⁽¹⁾	B-port input, A-port output	$t_r^{(2)} = t_f^{(2)} = 1$ ns	12	13	13	14	15	μ	
C (1)	A-port input, B-port output	C _L = 0, f = 10MHz,	12	13	13	14	15	pF	
C _{pdB} ⁽¹⁾	B-port input, A-port output	$t_r^{(2)} = t_f^{(2)} = 1$ ns	3	3	3	3	4	pr	

(1) Power-dissipation capacitance per transceiver

(2) t_r: Rise time; t_f: Fall time

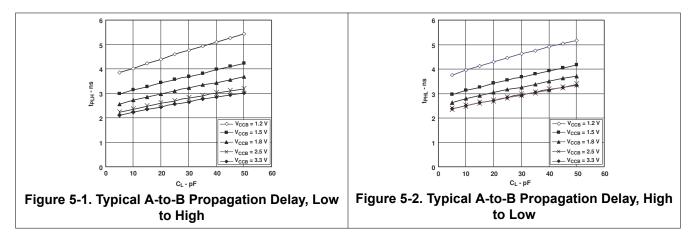


5.12 Typical Characteristics

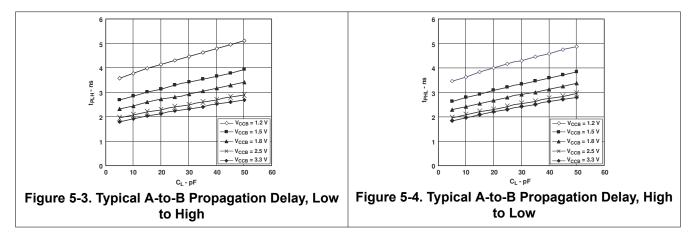
						007 00	
V _{CCB}		UNIT					
V CCB	0V	1.2V	1.5V	1.8V	2.5V	3.3V	UNIT
0V	0	<0.5	<0.5	<0.5	<0.5	<0.5	
1.2V	<0.5	<1	<1	<1	<1	1	
1.5V	<0.5	<1	<1	<1	<1	1	
1.8V	<0.5	<1	<1	<1	<1	<1	μA
2.5V	<0.5	1	<1	<1	<1	<1	
3.3V	<0.5	1	<1	<1	<1	<1	

Table 5-1. Typical Total Static Power Consumption (I_{CCA} + I_{CCB})

5.12.1 Typical Propagation Delay (A to B) vs Load Capacitance, $T_A = 25^{\circ}$ C, $V_{CCA} = 1.2V$

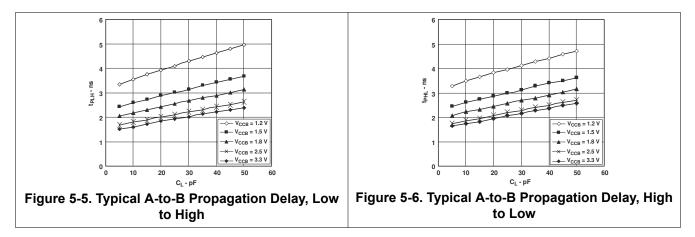


5.12.2 Typical Propagation Delay (A to B) vs Load Capacitance, $T_A = 25^{\circ}$ C, $V_{CCA} = 1.5V$

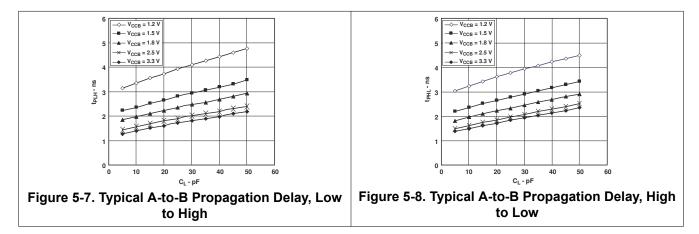




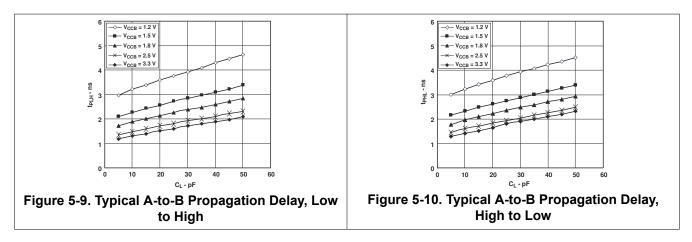
5.12.3 Typical Propagation Delay (A-to-B) vs Load Capacitance, $T_A = 25^{\circ}C$, $V_{CCA} = 1.8V$

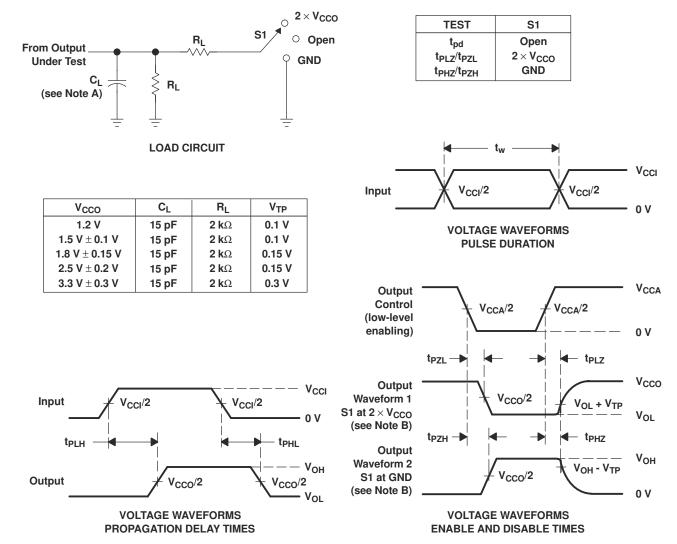


5.12.4 Typical Propagation Delay (A to B) vs Load Capacitance, $T_A = 25^{\circ}C$, $V_{CCA} = 2.5V$



5.12.5 Typical Propagation Delay (A to B) vs Load Capacitance, $T_A = 25^{\circ}C$, $V_{CCA} = 3.3V$





6 Parameter Measurement Information

NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , dv/dt \geq 1 V/ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. V_{CCI} is the V_{CC} associated with the input port.
- I. V_{CCO} is the V_{CC} associated with the output port.

Figure 6-1. Load Circuit and Voltage Waveforms



7 Detailed Description

7.1 Overview

This dual-bit noninverting bus transceiver uses two separate configurable power-supply rails. The A port is designed to track V_{CCA} and accepts any supply voltage from 1.2V to 3.6V. The B port is designed to track V_{CCB} and accepts any supply voltage from 1.2V to 3.6V. This allows for universal low-voltage bidirectional translation and level-shifting between any of the 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V voltage nodes.

The device is designed for asynchronous communication between two data buses. The logic levels of the direction-control (DIR) input activate either the B-port outputs or the A-port outputs. The device transmits data from the A bus to the B bus when the B-port outputs are activated and from the B bus to the A bus when the A-port outputs are activated. The input circuitry on both A and B ports always is active and must have a logic HIGH or LOW level applied to prevent excess internal leakage of the CMOS.

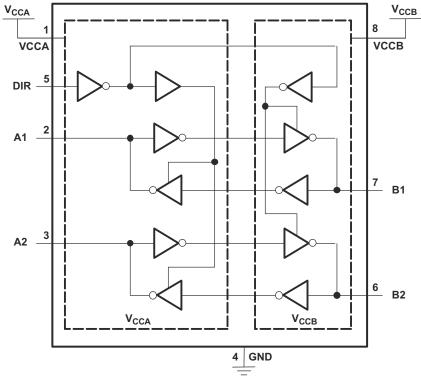
The device is designed so that the DIR input is powered by supply voltage from VCCA.

This device is fully specified for partial-power-down applications using off output current (I_{off}). The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when powered down.

The V_{CC} isolation feature makes sure that if either VCC input is at GND, both ports are put in a high-impedance state. This action prevents a false high or low logic being presented at the output.

NanoFree package technology is a major breakthrough in IC packaging concepts, using the die as the package.

7.2 Functional Block Diagram



Pin numbers are for the DCT and DCU packages only.



7.3 Feature Description

7.3.1 VCC Isolation

The V_{CC} isolation feature make sure that if either V_{CCA} or V_{CCB} are at GND, both ports are in a high-impedance state (I_{OZ} shown in *Electrical Characteristics*). This action prevents false logic levels from being presented to either bus.

7.3.2 2-Rail Design

Fully configurable 2-rail design allows each port to operate over the full 1.2V to 3.6V power-supply range.

7.3.3 IO Ports are 4.6-V Tolerant

The IO ports are up to 4.6 V tolerant.

7.3.4 Partial-Power-Down Mode

This device is fully specified for partial-power-down applications using off output current (I_{off}). The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when the device is powered down.

7.4 Device Functional Modes

Table 7-1 shows the functional modes of the SN74AVC2T45-Q1.

Table 7-1. Function Table (Each Transceiver)

INPUT DIR	OPERATION
L	B data to A bus
н	A data to B bus



8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

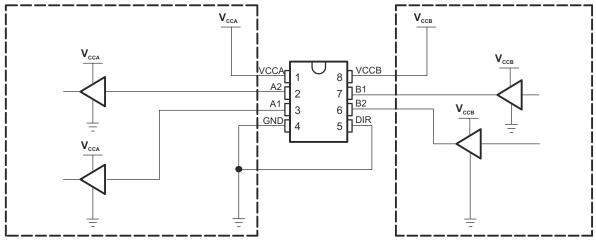
8.1 Application Information

The SN74AVC2T45 is used to shift IO voltage levels from one voltage domain to another. Bus A and bus B have independent power supplies, and a direction pin is used to control the direction of data flow. Unused data ports must not be floating; tie the unused port input and output to ground directly.

8.2 Typical Applications

8.2.1 Unidirectional Logic Level-Shifting Application

Figure 8-1 is an example circuit of the SN74AVC2T45 used in a unidirectional logic level-shifting application.



SYSTEM-1

SYSTEM-2

Figure 8-1. Unidirectional Logic Level-Shifting Application

8.2.1.1 Design Requirements

Table 8-1 lists the pins and pin descriptions of the SN74AVC2T45 connections with SYSTEM-1 and SYSTEM-2.

NAME	DESCRIPTION
VCCA	SYSTEM-1 supply voltage (1.2V to 3.6V)
A1	Output level depends on V _{CCA} .
A2	Output level depends on V _{CCA} .
GND	Device GND
DIR	The GND (low-level) determines B-port to A-port direction.
B2	Input threshold value depends on V _{CCB} .
B1	Input threshold value depends on V _{CCB} .
VCCB	SYSTEM-2 supply voltage (1.2V to 3.6V)
	NAME VCCA A1 A2 GND DIR B2 B1

Table 8-1. SN74AVC2T45 Pin Connections With SYSTEM-1 and SYSTEM-2

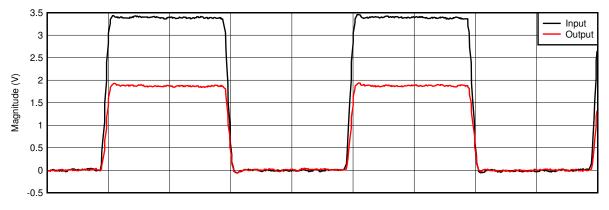
15



8.2.1.2 Detailed Design Procedure

This device uses drivers which are enabled depending on the state of the DIR pin. The designer must know the intended flow of data and take care not to violate any of the high or low logic levels. Unused data inputs must not be floating, as this can cause excessive internal leakage on the input CMOS structure. Make sure to tie any unused input and output ports directly to ground.

8.2.1.3 Application Curve



D001

Figure 8-2. 3.3 V to 1.8 V Level-Shifting With 1-MHz Square Wave

8.2.2 Bidirectional Logic Level-Shifting Application

Figure 8-3 shows the SN74AVC2T45 used in a bidirectional logic level-shifting application.

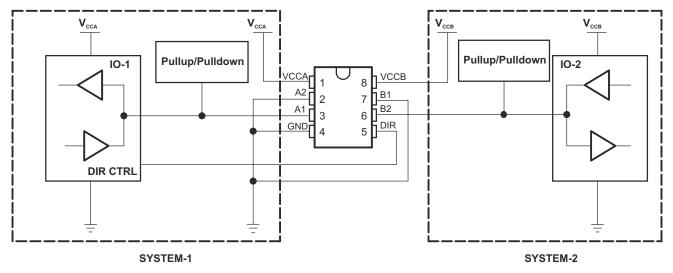


Figure 8-3. Bidirectional Logic Level-Shifting Application



8.2.2.1 Design Requirements

The SN74AVC2T45 does not have an output-enable (OE) pin, the system designer must take precautions to avoid bus contention between SYSTEM-1 and SYSTEM-2 when changing directions.

8.2.2.2 Detailed Design Procedure

Table 8-2 shows a sequence that illustrates data transmission from SYSTEM-1 to SYSTEM-2 and then from SYSTEM-2 to SYSTEM-1.

STATE	DIR CTRL	IO-1	IO-2	DESCRIPTION
1	н	Output	Input	SYSTEM-1 data to SYSTEM-2
2	Н	Hi-Z	Hi-Z	SYSTEM-2 is getting ready to send data to SYSTEM-1. IO-1 and IO-2 are disabled. The bus-line state depends on pullup or pulldown. ⁽¹⁾
3	L	Hi-Z	Hi-Z	DIR bit is flipped. IO-1 and IO-2 still are disabled. The bus-line state depends on pullup or pulldown. ⁽¹⁾
4	L	Input	Output	SYSTEM-2 data to SYSTEM-1

(1) SYSTEM-1 and SYSTEM-2 must use the same conditions, that is, both pullup or both pulldown.

8.2.2.2.1 Enable Times

Calculate the enable times for the SN74AVC2T45 using the following formulas:

- t_{PZH} (DIR to A) = t_{PLZ} (DIR to B) + t_{PLH} (B to A)
- t_{PZL} (DIR to A) = t_{PHZ} (DIR to B) + t_{PHL} (B to A)
- t_{PZH} (DIR to B) = t_{PLZ} (DIR to A) + t_{PLH} (A to B)
- t_{PZL} (DIR to B) = t_{PHZ} (DIR to A) + t_{PHL} (A to B)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the SN74AVC2T45 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled before presenting the device with an input. After the B port has been disabled, an input signal applied to the port appears on the corresponding A port after the specified propagation delay.

8.3 Power Supply Recommendations

A proper power-up sequence must always be followed to avoid excessive current on the supply pin, bus contention, oscillations, or other anomalies. To guard against such power-up problems, take the following precautions:

- 1. Connect ground before any supply voltage is applied.
- 2. Power up V_{CCA}.
- 3. V_{CCB} can be ramped up along with or after V_{CCA} .



8.4 Layout

8.4.1 Layout Guidelines

To verify the reliability of the device, follow common printed-circuit board layout guidelines.

- Bypass capacitors can be used on power supplies. Place the capacitors as close as possible to the VCCA, VCCB pin and GND pin.
- Short trace lengths can be used to avoid excessive loading.

8.4.2 Layout Example

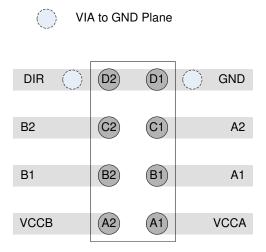


Figure 8-4. Layout Example for YZP Package



9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation see the following:

• Texas Instruments, Implications of Slow or Floating CMOS Inputs

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

NanoFree[™] is a trademark of Texas Instruments.

TI E2E[™] is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision M (September 2024) to Revision N (February 2025)	Page
•	Updated DCT and DDF Thermal Information	6

С	hanges from Revision L (May 2017) to Revision M (September 2024)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
•	Added DDF package	1
•	Deleted the Community Resources section	19
•	Added the Support Resources, Receiving Notification of Documentation Updates, Electrostatic Dischar	
	Statement, and Glossary sections	19

20 Submit Document Feedback

Changes from Revision K (April 2015) to Revision L (May 2017)

Changes from Revision J (June 2007) to Revision K (April 2015)

Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



Page



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AVC2T45DCTR	ACTIVE	SSOP	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	DT2 Z	Samples
SN74AVC2T45DCTRE4	ACTIVE	SSOP	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	DT2 Z	Samples
SN74AVC2T45DCTT	ACTIVE	SSOP	DCT	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	DT2 Z	Samples
SN74AVC2T45DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(DT2R, T2) DZ	Samples
SN74AVC2T45DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	DT2R	Samples
SN74AVC2T45DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	DT2R	Samples
SN74AVC2T45DCUTG4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	DT2R	Samples
SN74AVC2T45DDFR	ACTIVE	SOT-23-THIN	DDF	8	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	A2T45	Samples
SN74AVC2T45YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	TDN	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



www.ti.com

PACKAGE OPTION ADDENDUM

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74AVC2T45 :

Automotive : SN74AVC2T45-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



Texas

NSTRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AVC2T45DCTR	SSOP	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74AVC2T45DCTT	SSOP	DCT	8	250	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74AVC2T45DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.25	3.4	1.0	4.0	8.0	Q3
SN74AVC2T45DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74AVC2T45DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74AVC2T45DDFR	SOT-23- THIN	DDF	8	3000	180.0	8.4	3.2	3.1	1.25	4.0	8.0	Q3
SN74AVC2T45YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1



www.ti.com

PACKAGE MATERIALS INFORMATION

3-Feb-2025



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AVC2T45DCTR	SSOP	DCT	8	3000	182.0	182.0	20.0
SN74AVC2T45DCTT	SSOP	DCT	8	250	182.0	182.0	20.0
SN74AVC2T45DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
SN74AVC2T45DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74AVC2T45DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74AVC2T45DDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
SN74AVC2T45YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

DCU0008A



PACKAGE OUTLINE

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side. 4. Reference JEDEC registration MO-187 variation CA.



DCU0008A

EXAMPLE BOARD LAYOUT

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DCU0008A

EXAMPLE STENCIL DESIGN

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

8. Board assembly site may have different recommendations for stencil design.



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

DCT0008A



PACKAGE OUTLINE

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.



DCT0008A

EXAMPLE BOARD LAYOUT

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

Publication IPC-7351 may have alternate designs.
 Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DCT0008A

EXAMPLE STENCIL DESIGN

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

8. Board assembly site may have different recommendations for stencil design.



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

DDF0008A



PACKAGE OUTLINE

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.



DDF0008A

EXAMPLE BOARD LAYOUT

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



4. Publication IPC-7351 may have alternate designs.

5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DDF0008A

EXAMPLE STENCIL DESIGN

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



^{6.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



^{7.} Board assembly site may have different recommendations for stencil design.

YZP0008



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



YZP0008

EXAMPLE BOARD LAYOUT

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



YZP0008

EXAMPLE STENCIL DESIGN

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025, Texas Instruments Incorporated